

CIR-W4DUSW2108G

DDR4 WIDE TEMP. DIMM 2133MHz 8GB

Description	Specifications	
CIR-W4DUSW2108G is a CMOS Double Data Rate IV (DDR4) Synchronous DRAM module, in Fine Ball Grid Array(FBGA) packages on a 288pin glass-epoxy substrate. DDR4 unbuffered UDIMM series offers fully synchronous operations referenced to both rising and falling edges of the clock. The data paths are internally pipelined and 8-bit prefetched to achieve very high bandwidth.	Density	8GB
	Pin Count	288pin
	Type	Unbuffered
	Dimensions	133.35mm x 31.25mm
	ECC	Non-ECC
	Component Config	1G x 8 bit
	Data Rate	2133 MHz
	CAS Latency	15
	Voltage	1.2V
	PCB Layers	8
	Operating Temp.(TCASE)	-40°C~+95°C
	Module Ranks	Single Rank

Features

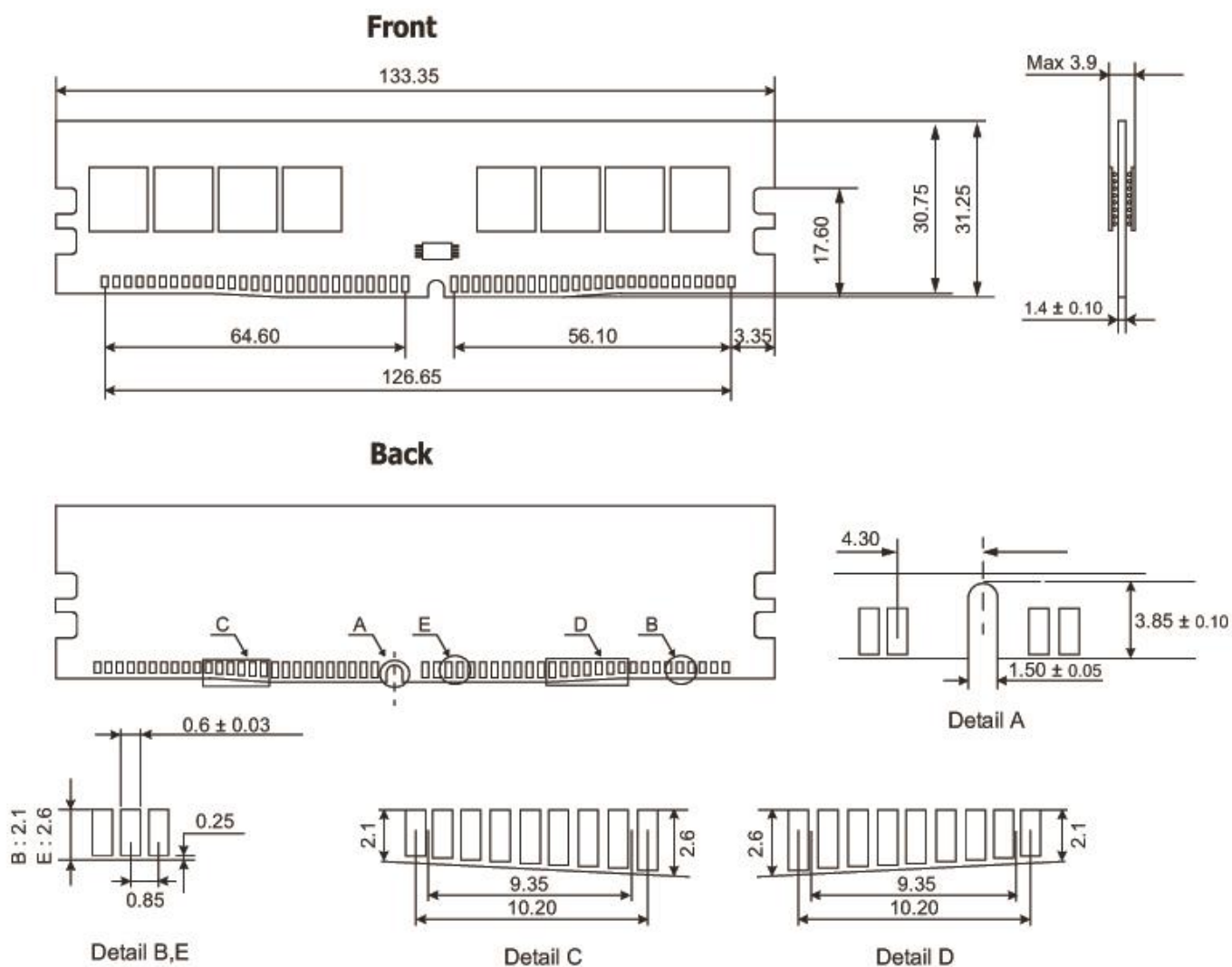
- JEDEC standard
- VDD=VDDQ = 1.2V±0.06V (1.14V~1.26V)
- Programmable CAS Latency(posted CAS): 11,12,13,14,15
- 8-bit pre-fetch
- 16 Banks (4 Bank Groups)
- Internal(self) calibration : Internal self calibration through ZQ pin
- On Die Termination using ODT pin
- Average Refresh Period
- 7.8us (TCASE ≤ 95°C)
- Asynchronous Reset pin supported
- Burst Length: 8 or BC4
- POD (Pseudo Open Drain) interface for data input/output
- Serial presence detect (SPD)
- All of products are Halogen-free
- All of Lead-Free products are compliant for RoHS

Speed Grade

Frequency Grade	Data Transfer Rate	CAS Latency Support					CL-tRCD-tRP
		CL11	CL12	CL13	CL14	CL15	
DDR4-2133	PC4-17000	1600	1600	1866	1866	2133	15-15-15

Package Dimensions

Unit: mm



Tolerances : ± 0.15 mm unless otherwise specified